

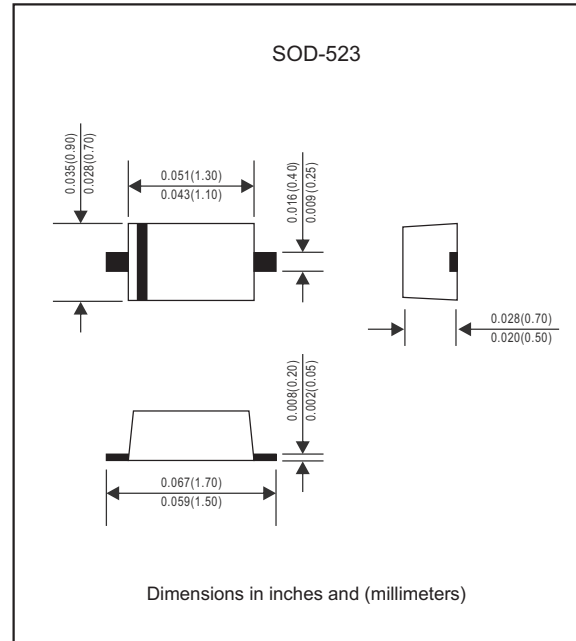
Features

- Low power loss, high efficiency.
- High current capability, low forward voltage drop.
- High surge capability.
- Guardring for overvoltage protection.
- Very tiny plastic SMD package.
- Ultra high-speed switching.
- Silicon epitaxial planar chip, metal silicon junction.
- Lead-free parts meet environmental standards of MIL-STD-19500 /228
- Compliant to Halogen-free
- Suffix "-Q1" for AEC-Q101

Mechanical data

- Epoxy:UL94-V0 rated flame retardant
- Case : Molded plastic, SOD-523
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Polarity : Indicated by cathode band
- Mounting Position : Any

Package outline



Maximum ratings and Electrical Characteristics (AT $T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Forward rectified current	See Fig.1	I_O			1.0	A
Forward surge current	8.3ms single half sine-wave (JEDEC methode)	I_{FSM}			6	A
Reverse current	$V_R = V_{RRM}$ $T_J = 25^{\circ}\text{C}$	I_R			0.1	mA
Diode junction capacitance	$V_R = 0\text{ V}$, $f = 1\text{MHz}$	C_J		50		pF
Storage temperature		T_{STG}	-50		+125	$^{\circ}\text{C}$

SYMBOLS	V_{RRM}^{*1} (V)	V_{RMS}^{*2} (V)	V_R^{*3} (V)	V_F^{*4} (V)	Operating temperature T_J , ($^{\circ}\text{C}$)
B5819WT-Q1	40	28	40	0.80	-40 to +125

*1 Repetitive peak reverse voltage

*2 RMS voltage

*3 Continuous reverse voltage

*4 Maximum forward voltage@ $I_F=1.0\text{A}$

Rating and characteristic curves

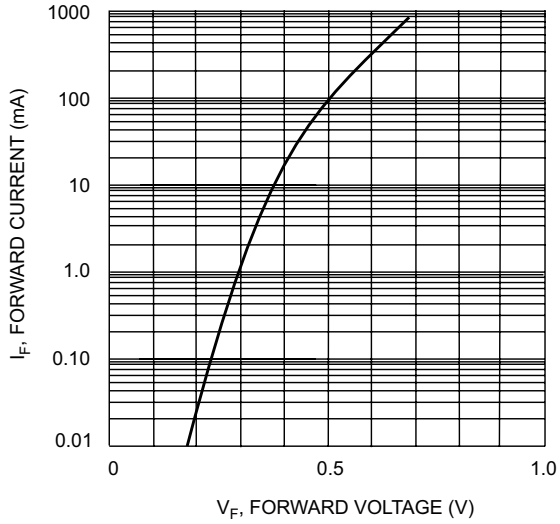


Fig. 1 Typical Forward Characteristics

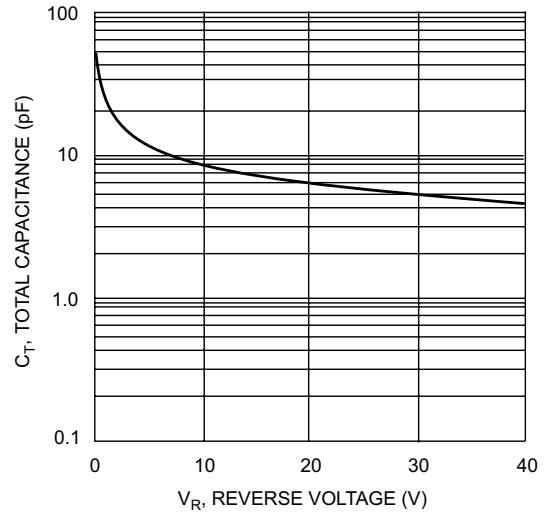




Fig. 2 Typ. Total Capacitance vs Reverse Voltage



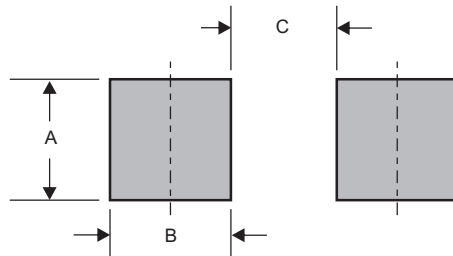
Pinning information

Pin	Simplified outline	Symbol
Pin1 cathode Pin2 anode		

Marking

Type number	Marking code
B5819WT-Q1	4A/KX

Suggested solder pad layout



Dimensions in inches and (millimeters)

PACKAGE	A	B	C
SOD-523	0.032 (0.80)	0.024 (0.60)	0.044 (1.10)